

MTD3055V

N-Channel Enhancement Mode Field Effect Transistor

General Description

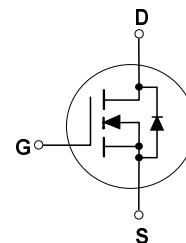
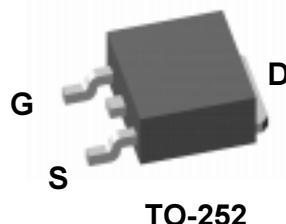
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 12 A, 60 V. $R_{DS(ON)} = 0.15 \Omega$ @ $V_{GS} = 10$ V
- Low gate charge.
- Fast switching speed.
- High performance technology for low $R_{DS(ON)}$.



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Maximum Drain Current -Continuous $T_C = 100^\circ\text{C}$ (Note 1)	12	A
		7.3	
	Maximum Drain Current -Pulsed	37	
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ (Note 1)	48	W
	$T_A = 25^\circ\text{C}$ (Note 1a)	3.9	
	$T_A = 25^\circ\text{C}$ (Note 1b)	1.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Thermal Characteristics

R_{QJC}	Thermal Resistance, Junction-to- Case (Note 1)	3.13	°C/W
R_{QJA}	Thermal Resistance, Junction-to- Ambient (Note 1a)	38	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
MTD3055V	MTD3055V	13"	16mm	2500

* Die and manufacturing source subject to change without prior notification.

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
DRAIN-SOURCE AVALANCHE RATINGS (Note 2)						
W_{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25\text{ V}$, $I_D = 12\text{ A}$			72	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				12	A
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	60			V
ΔBV_{DSS} ΔT_J	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		42		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$			10	μA
		$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150^\circ\text{C}$			100	
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}$, $V_{DS} = 0\text{ V}$			-100	nA
On Characteristics (Note 2)						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	2.8	4	V
$\Delta V_{GS(\text{th})}$ ΔT_J	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		-2.3		mV/ $^\circ\text{C}$
$R_{DS(\text{on})}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$, $I_D = 6\text{ A}$			0.15	Ω
$V_{DS(\text{on})}$	Drain-Source On-Voltage On-Resistance	$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$ $V_{GS} = 10\text{ V}$, $I_D = 6\text{ A}$, $T_J = 150^\circ\text{C}$			2.2 1.9	V
g_{FS}	Forward Transconductance	$V_{DS} = 7\text{ V}$, $I_D = 6\text{ A}$	4.0			s
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$			500	pF
C_{oss}	Output Capacitance				180	pF
C_{rss}	Reverse Transfer Capacitance				50	pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{\text{GEN}} = 9.1\text{ }\Omega$			10	ns
t_r	Turn-On Rise Time				60	ns
$t_{d(off)}$	Turn-Off Delay Time				30	ns
t_f	Turn-Off Fall Time				50	ns
Q_g	Total Gate Charge	$V_{DS} = 48\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 10\text{ V}$		12.7	17	nC
Q_{gs}	Gate-Source Charge			3.2		nC
Q_{gd}	Gate-Drain Charge			7		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Maximum Continuous Drain-Source Diode Forward Current (Note 2)				12	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current (Note 2)				37	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_s = 12\text{ A}$	(Note 2)		1.6	V
t_{rr}	Drain-Source Reverse Recovery Time	$I_F = 12\text{ A}$, $di/dt = 100\text{A}/\mu\text{s}$		46		ns

Notes:

- $R_{\theta_{JA}}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the drain tab.
 $R_{\theta_{JC}}$ is guaranteed by design while $R_{\theta_{CA}}$ is determined by the user's board design.



- a) $R_{\theta_{JA}} = 38^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2oz copper.

- b) $R_{\theta_{JA}} = 96^\circ\text{C}/\text{W}$ when mounted on a minimum pad.

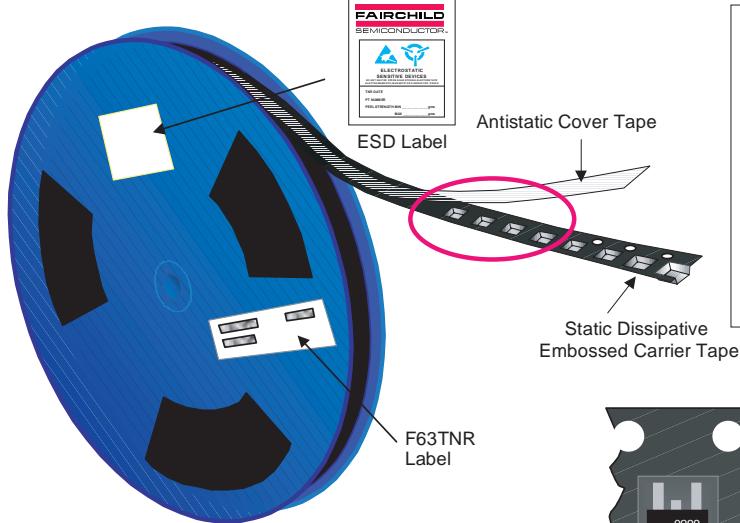
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

TO-252 Tape and Reel Data and Package Dimensions

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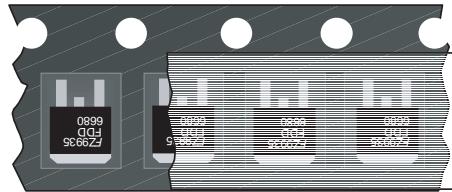
D-PAK (TO-252) Packaging Configuration: Figure 1.0



Packaging Description:

TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2500 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). This and some other options are further described in the Packaging Information table.

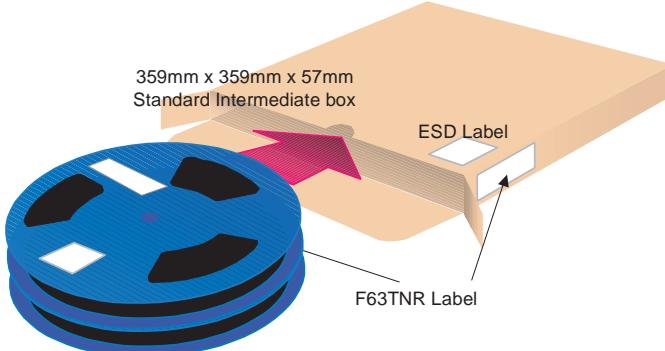
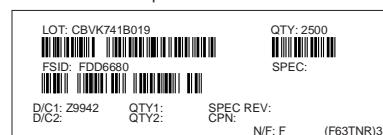
These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



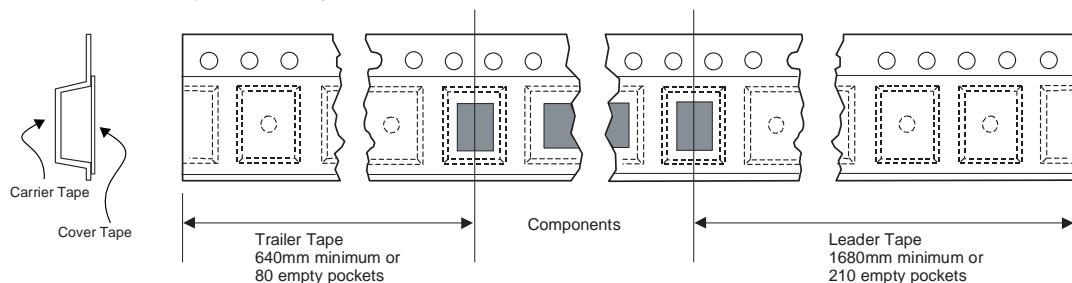
D-PAK (TO-252) Unit Orientation

D-PAK (TO-252) Packaging Information	
Packaging Option	Standard (no flow code)
Packaging type	TNR
Qty per Reel/Tube/Bag	2,500
Reel Size	13" Dia
Box Dimension (mm)	359x359x57
Max qty per Box	5,000
Weight per unit (gm)	0.300
Weight per Reel(kg)	1.200
Note/Comments	

F63TNR Label sample



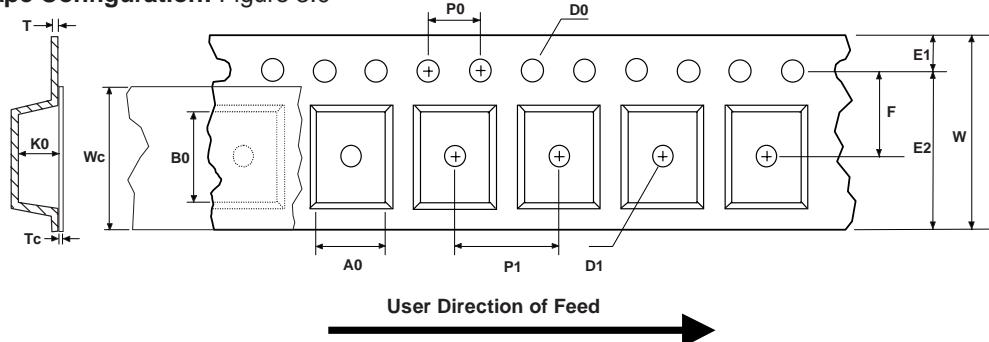
TO-252 (D-PAK) Tape Leader and Trailer Configuration: Figure 2.0



TO-252 Tape and Reel Data and Package Dimensions

D-PAK (TO-252) Embossed Carrier

Tape Configuration: Figure 3.0



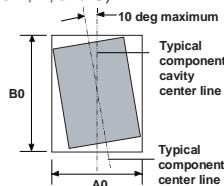
Dimensions are in millimeter

Pkg type	A_0	B_0	W	D_0	D_1	E_1	E_2	F	P_1	P_0	K_0	T	W_c	T_c
TO252 (24mm)	6.90 $+/-.10$	10.50 $+/-.10$	16.0 $+/-.3$	1.55 $+/-.05$	1.5 $+/-.10$	1.75 $+/-.10$	14.25 min	7.50 $+/-.10$	8.0 $+/-.1$	4.0 $+/-.1$	2.65 $+/-.10$	0.30 $+/-.05$	13.0 $+/-.3$	0.06 $+/-.02$

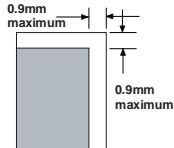
Notes: A_0 , B_0 , and K_0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

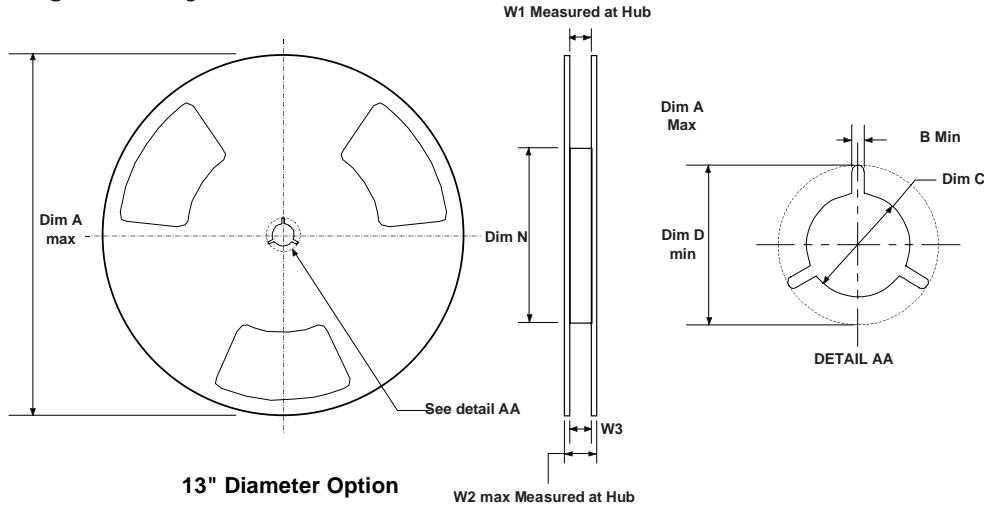


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

D-PAK (TO-252) Reel Configuration: Figure 4.0



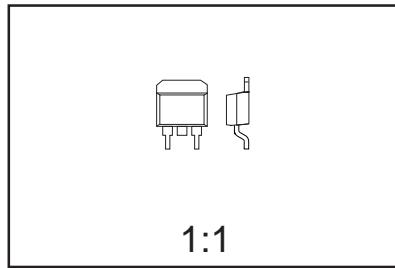
13" Diameter Option

Dimensions are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 - 0.764 15.9 - 19.4

TO-252 Tape and Reel Data and Package Dimensions

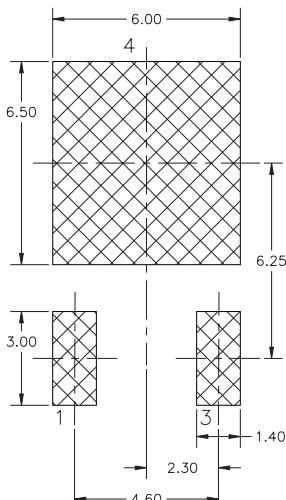
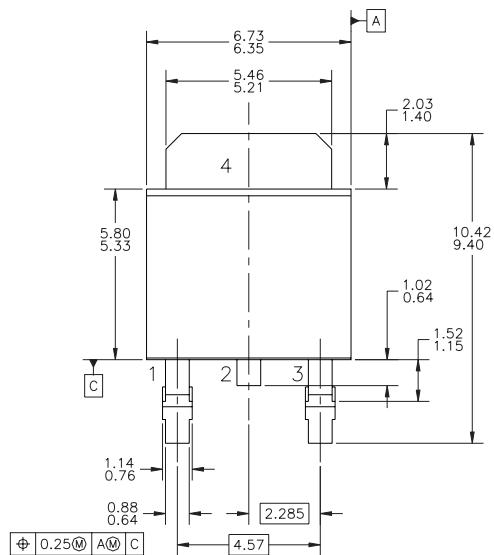
TO-252 (FS PKG Code AA)



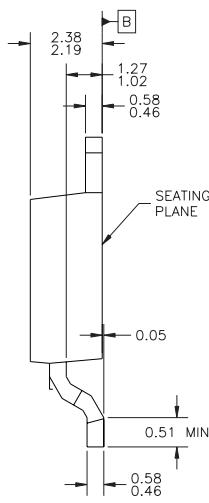
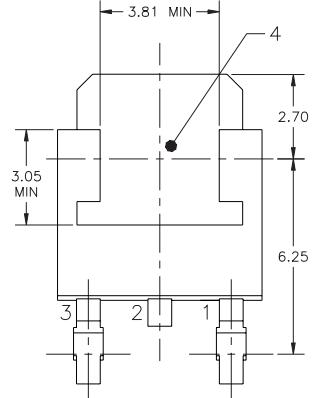
Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.300



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.

B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE B, VARIATION AB, ITEM 10.268, DATED SEPTEMBER 1988.

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